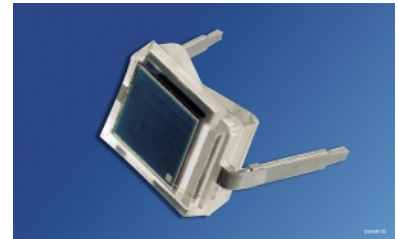


Silizium-Fotodiode Silicon Photodiode

BPW 33



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 350 nm bis 1100 nm
- Sperrstromarm (typ. 20 pA)
- DIL-Plastikbauform mit hoher Packungsdichte

Anwendungen

- Belichtungsmesser
- Farbanalyse

Features

- Especially suitable for applications from 350 nm to 1100 nm
- Low reverse current (typ. 20 pA)
- DIL plastic package with high packing density

Applications

- Exposure meters
- Color analysis

Typ Type	Bestellnummer Ordering Code
BPW 33	Q62702-P76

Grenzwerte**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 85	°C
Sperrspannung Reverse voltage	V_R	7	V
Verlustleistung, $T_A = 25\text{ °C}$ Total power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)**Characteristics** ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5\text{ V}$ Spectral sensitivity	S	75 (≥ 35)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\max}$	800	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{\max} Spectral range of sensitivity $S = 10\%$ of S_{\max}	λ	350 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.34	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.71 × 2.71	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	0.5	mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Dunkelstrom, $V_R = 1\text{ V}$ Dark current	I_R	20 (≤ 100)	pA
Nullpunktsteilheit, $E = 0$ Zero crossover	S_0	≤ 2.5	pA/mV
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.59	A/W

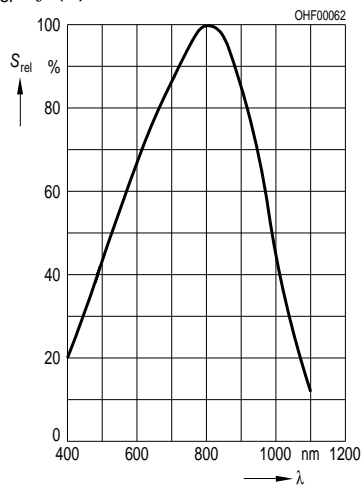
Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

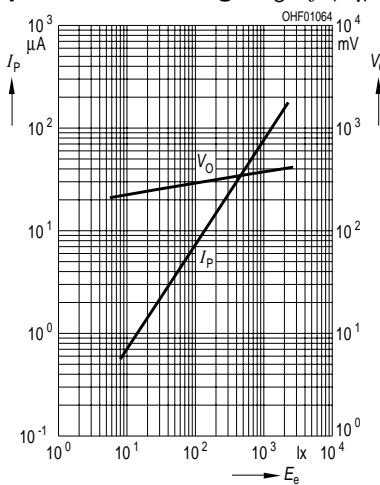
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.86	<u>Electrons</u> Photon
Leerlaufspannung, $E_V = 1000\text{ lx}$ Open-circuit voltage	V_O	440 (≥ 375)	mV
Kurzschlußstrom, $E_V = 1000\text{ lx}$ Short-circuit current	I_{SC}	72	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 1\text{ k}\Omega$; $V_R = 5\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 70\text{ }\mu\text{A}$	t_r, t_f	1.5	μs
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	630	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	-2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 1\text{ V}$, $\lambda = 850\text{ nm}$	NEP	4.3×10^{-15}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 1\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	6.3×10^{13}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

Relative Spectral Sensitivity

$S_{rel} = f(\lambda)$

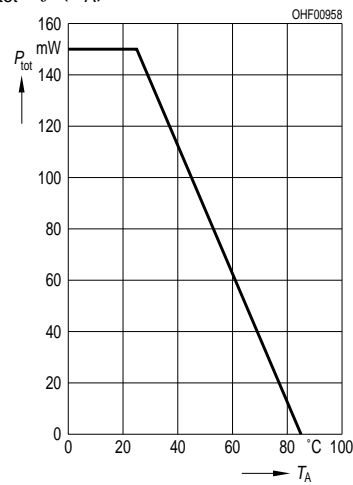


**Photocurrent $I_P = f(E_e)$, $V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_e)$**



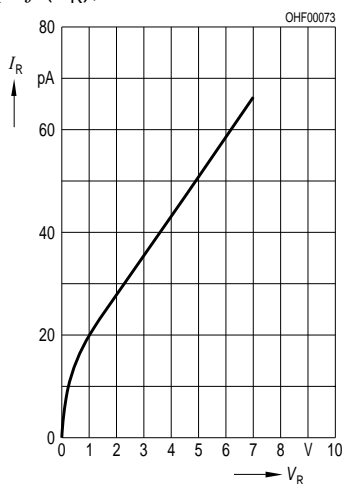
Total Power Dissipation

$P_{tot} = f(T_A)$



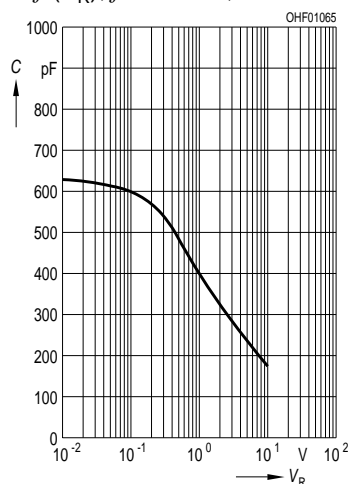
Dark Current

$I_R = f(V_R), E = 0$



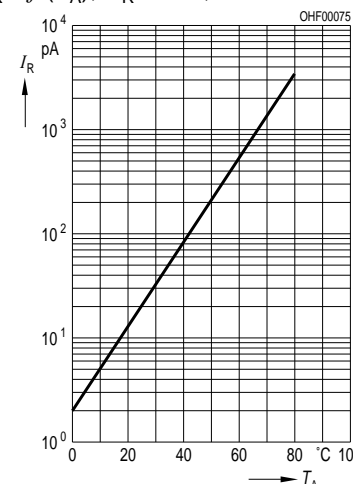
Capacitance

$C = f(V_R), f = 1 MHz, E = 0$



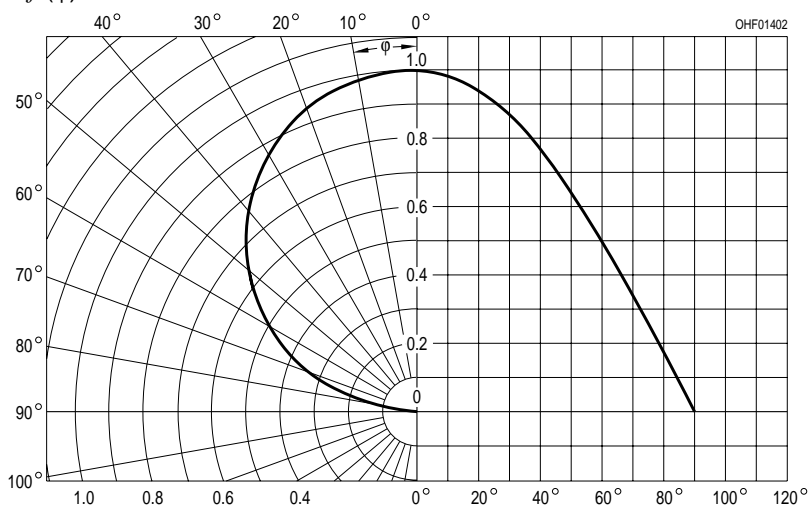
Dark Current

$I_R = f(T_A), V_R = 1 V, E = 0$

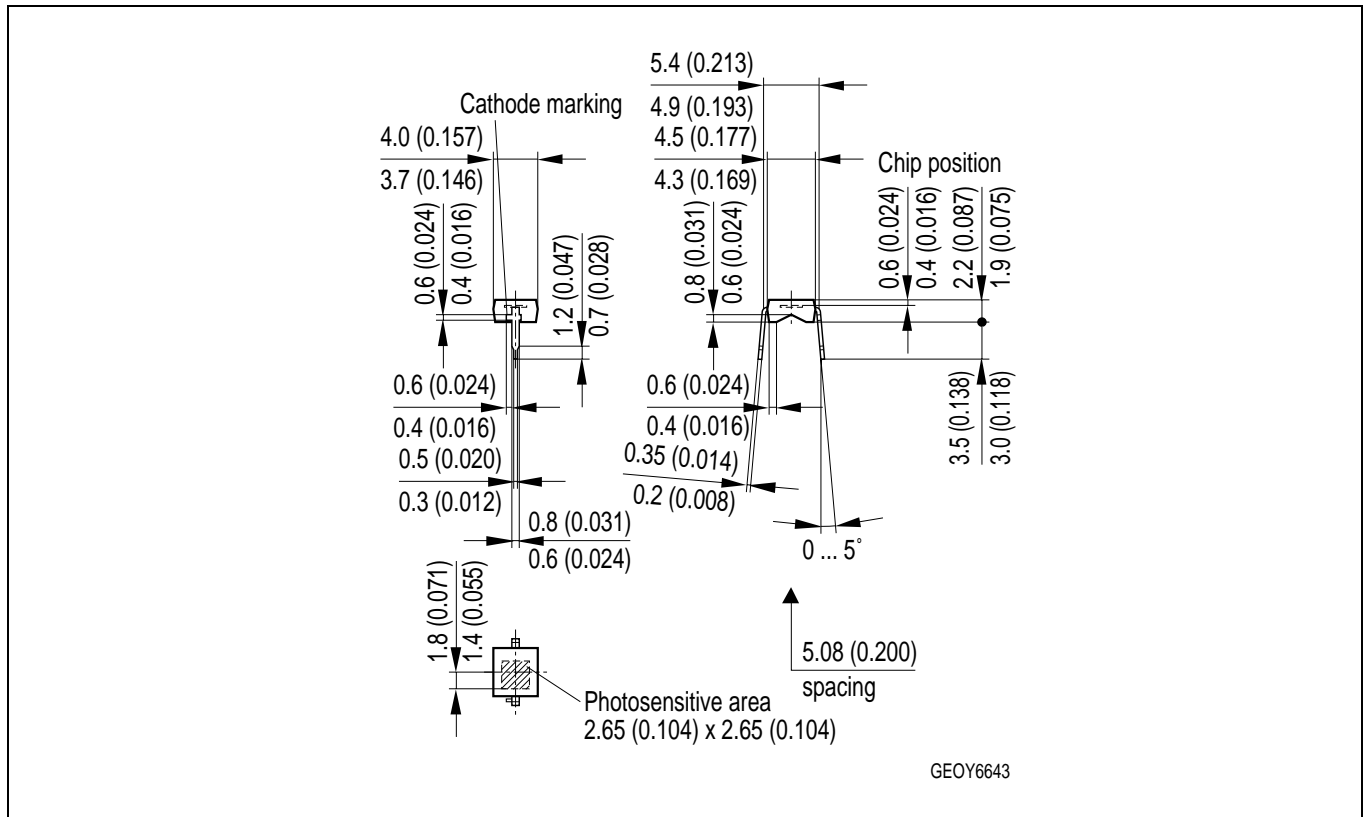


Directional Characteristics

$S_{rel} = f(\phi)$



**Maßzeichnung
Package Outlines**



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

**Published by OSRAM Opto Semiconductors GmbH & Co. OHG
Wernerwerkstrasse 2, D-93049 Regensburg**

© All Rights Reserved.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components ¹, may only be used in life-support devices or systems ² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.